ABSTRACT

The invention relates to a method of forming a structure comprising a layer chosen among semiconductor materials from a donor wafer, the method comprising the following steps:

(a) implanting atomic species to form a weakness zone in the donor wafer to a depth close to the thickness of the layer to be removed;

(b) bonding the donor wafer to a host wafer;

(c) supplying energy so as to disunite the taken-off layer from the donor wafer at the weakness zone;

(d) treating the taken-off layer;

wherein step (d) comprises a recovering operation of the taken-off layer carried out when the taken-off layer is still in contact with the remaining part of the donor wafer, and in that the recovering operation is applied by means of heat treatment at a temperature lower than the re-adhesion temperature of the taken-off layer with the remaining part of the donor wafer.

FIGURE 3d

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